MC74HC4067A

Quad Analog Switch/ Multiplexer/Demultiplexer

High−Performance Silicon−Gate CMOS

The MC74HC4067A utilizes silicon−gate CMOS technology to achieve fast propagation delays, low ON resistances, and low OFF−channel leakage current. This bilateral switch/ multiplexer/demultiplexer controls analog and digital voltages that may vary across the full power−supply range (from V_{CC} to GND).

The ON/OFF control inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs. For analog switches with voltage−level translators, see the HC4316A.

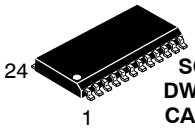
Features

- Fast Switching and Propagation Speeds
- High ON/OFF Output Voltage Ratio
- Low Crosstalk Between Switches
- Diode Protection on All Inputs/Outputs
- Wide Power−Supply Voltage Range (V_{CC} − GND) = 2.0 to 6.0 V
- Analog Input Voltage Range (V_{CC} − GND) = 0 to 6.0 V
- Improved Linearity and Lower ON Resistance over Input Voltage
- Low Noise
- These are Pb−Free Devices

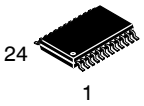
ON Semiconductor®

http://onsemi.com

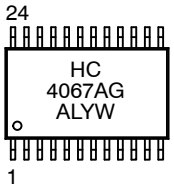
MARKING DIAGRAMS



SOIC−24
DW SUFFIX
CASE 751E



TSSOP−24
DT SUFFIX
CASE 948H



A	= Assembly Location
L, WL	= Wafer Lot
Y, YY	= Year
W, WW	= Work Week
G	= Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 10 of this data sheet.

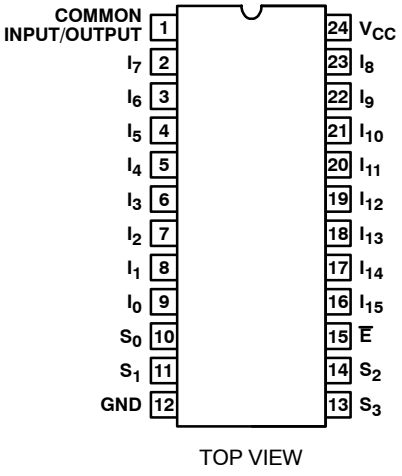


Figure 1. Pin Assignment

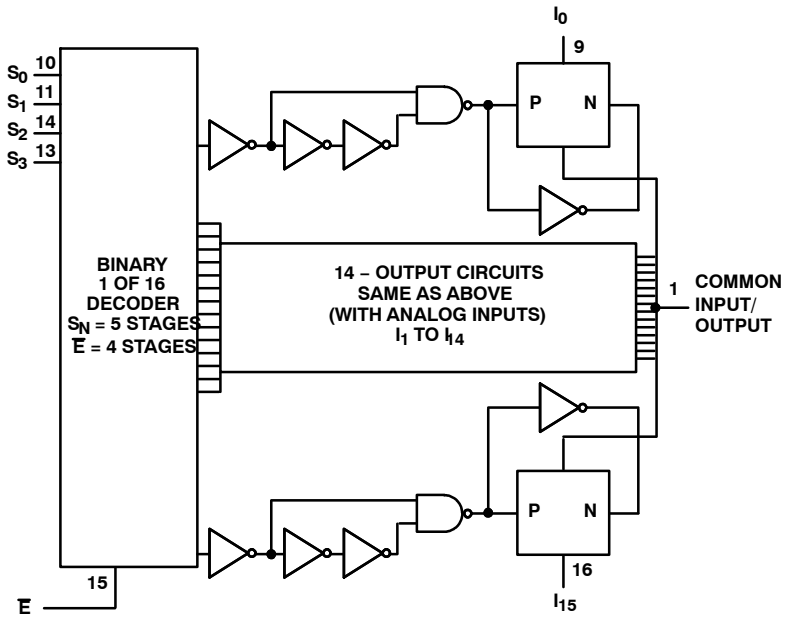


Figure 2. Function Diagram

TRUTH TABLE

S0	S1	S2	S3	$\overline{E}$	SELECTED CHANNEL
X	X	X	X	1	None
0	0	0	0	0	0
1	0	0	0	0	1
0	1	0	0	0	2
1	1	0	0	0	3
0	0	1	0	0	4
1	0	1	0	0	5
0	1	1	0	0	6
1	1	1	0	0	7
0	0	0	1	0	8
1	0	0	1	0	9
0	1	0	1	0	10
1	1	0	1	0	11
0	0	1	1	0	12
1	0	1	1	0	13
0	1	1	1	0	14
1	1	1	1	0	15

H= High Level
L= Low Level
X= Don't Care

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +7.0	V
V_{IS}	Analog Input Voltage		−0.5 to V_{CC} + 0.5	V
V_{IN}	Digital Input Voltage		−0.5 to V_{CC} + 0.5	V
I_{IK}	Input Clamping Current	V_{IN} < −0.5 V or V_{IN} > V_{CC} + 0.5 V	±20	mA
I_{SK}	Switch Input Clamping Current	V_{IS} < −0.5 V or V_{IS} > V_{CC} + 0.5 V	±20	mA
I_{IS}	DC Switch Current		±25	mA
I_O	DC Output Source / Sink Current		±25	mA
I_{CC}	DC Supply Current per Supply Pin		±100	mA
I_{GND}	DC Ground Current per Ground Pin		±100	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
T_J	Junction Temperature under Bias		+150	°C
θ_{JA}	Thermal Resistance	SOIC TSSOP	97 148	°C/W
P_D	Power Dissipation in Still Air at 85°C	SOIC TSSOP	500 450	mW
MSL	Moisture Sensitivity		Level 1	
F_R	Flammability Rating	Oxygen Index: 30% − 35%	UL−94−VO (0.125 in)	
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 1) Machine Model (Note 2)	>3000 >200	V
$I_{Latchup}$	Latchup Performance	Above V_{CC} and Below GND at 85°C (Note 3)	±100	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Tested to EIA/JESD22−A114−A.
2. Tested to EIA/JESD22−A115−A.
3. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	Positive DC Supply Voltage (Referenced to GND)		2.0	6.0	V
V_{IS}	Analog Input Voltage (Referenced to GND)		GND	V_{CC}	V
V_{in}	Digital Input Voltage (Referenced to GND)		GND	V_{CC}	V
V_{IO}*	Static or Dynamic Voltage Across Switch		−	1.2	V
T_A	Operating Temperature, All Package Types		−55	+125	°C
t_r, t_f	Input Rise and Fall Rate (Digital Inputs)	V_{CC} = 2.0 V V_{CC} = 3.0 V V_{CC} = 4.5 V V_{CC} = 6.0 V	0 0 0 0	1000 600 500 400	ns

*For voltage drops across the switch greater than 1.2 V (switch on), excessive V_{CC} current may be drawn; i.e., the current out of the switch may contain both V_{CC} and switch input components. The reliability of the device will be unaffected unless the Maximum Ratings are exceeded.

DC ELECTRICAL CHARACTERISTIC Digital Section (Voltages Referenced to GND)

Symbol	Parameter	Conditions	V_{CC} (V)	Guaranteed Limit							Unit
				25°C			−40 to 85°C		−55 to 125°C		
				Min	Typ	Max	Min	Max	Min	Max	
V_{IH}	Minimum High−Level Input Voltage, Channel−Select or Enable Inputs		2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2			1.5 2.1 3.15 4.2			1.5 2.1 3.15 4.2	V
V_{IL}	Maximum Low−Level Input Voltage, Channel−Select or Enable Inputs		2.0 3.0 4.5 6.0			0.5 0.9 1.35 1.8		0.5 0.9 1.35 1.8		0.5 0.9 1.35 1.8	V
I_{IN}	Input Leakage Current, Control Inputs	$V_{IN} = V_{CC}$ or GND	6.0			±0.1		±1.0		±1.0	μA
I_{CC}	Maximum Supply Current per Package	$V_{IN} = V_{CC}$ or GND, I_O=0 V_{IS} = GND or V_{CC}, $V_{OS} = V_{CC}$ or GND	6.0			4.0		40		80	μA
R_{ON}	ON Resistance	I_O = 1 mA $V_{IN} = V_{CC}$ or GND, $V_{IS} = V_{CC}$ or GND	4.5 6.0		70 60	160 140		200 175		240 210	Ω
$R_{ON(peak)}$	ON Resistance (peak)	I_O = 1 mA $V_{IN} = V_{CC}$ to GND, $V_{IS} = V_{CC}$ to GND	4.5 6.0		90 80	180 160		225 200		270 240	Ω
ΔR_{on}	ON Resistance Mismatch Between Any 2 Switches		4.5 6.0		10 8.5						Ω
I_{OFF}	OFF−State Leakage Current, All Channels	SW OFF, $V_{IS} = V_{CC}$ or GND	6.0			±0.8		±8		±8	μA
I_{ON}	ON−State Leakage Current	SW OFF, $V_{IS} = V_{CC}$ or GND	6.0			±0.8		±8		±8	μA

AC CHARACTERISTICS (INPUT t_r, t_f = 6 ns)

Symbol	Parameter	Conditions	V_{CC} (V)	Guaranteed Limits							Unit
				25°C			–40 to 85°C		–55 to 125°C		
				Min	Typ	Max	Min	Max	Min	Max	
t_{PLH}, t_{PHL}	Propagation Delay Switch In to Out	C_L = 50 pF	2.0 4.5 6.0			75 15 13		95 19 16		110 22 19	ns
		C_L = 15 pF	5.0		6.0						
t_{ON}	Switch Turn–ON Time										ns
	$\overline{E}$ to Out	C_L = 50 pF	2.0 4.5 6.0			275 55 47		345 69 59		415 83 71	
		C_L = 15 pF	5.0		23						
	SN to Out	C_L = 50 pF	2.0 4.5 6.0			300 60 51		375 75 64		450 90 76	
		C_L = 15 pF	5.0		25						
t_{OFF}	Switch Turn–OFF Time										ns
	$\overline{E}$ to Out	C_L = 50 pF	2.0 4.5 6.0			275 55 47		345 69 59		415 83 71	
		C_L = 15 pF	5.0		23						
	SN to Out	C_L = 50 pF	2.0 4.5 6.0			290 58 49		365 73 62		435 87 74	
		C_L = 15 pF	5.0		21						
C_{in}	Input Capacitance, Control Pins				3.5	10		10		10	pF
C_{PD}	Power Dissipation Capacitance (Note 4)	C_L = 15 pF	5.0			29					pF

4. C_{PD} is used to determine the dynamic power consumption, per multivibrator.

ANALOG SWITCH CHANNEL CHARACTERISTICS

Symbol	Parameter	Conditions	V_{CC} (V)	Limit* 25°C	Unit
BW	Maximum On−Channel Bandwidth or Minimum Frequency Response	f_{in} = 1 MHz Sine Wave Adjust f_{in} Voltage to Obtain 0 dBm at V_{OS} Increase f_{in} Frequency Until dB Meter Reads − 3 dB R_L = 50 Ω, C_L = 10 pF	4.5	90	MHz
−	Off−Channel Feedthrough Isolation	$f_{in} \equiv$ Sine Wave Adjust f_{in} Voltage to Obtain 0 dBm at V_{IS} f_{in} = 10 kHz, R_L = 600 Ω, C_L = 50 pF f_{in} = 1.0 MHz, R_L = 50 Ω, C_L = 10 pF	 4.5 4.5	 −65 −75	dB
−	Feedthrough Noise $\overline{E}$, Sn to Switch	$V_{in} \leq$ 1 MHz Square Wave ($t_r = t_f$ = 6 ns) Adjust R_L at Setup so that I_S = 0 A R_L = 600 Ω, C_L = 50 pF R_L = 10 kΩ, C_L = 10 pF	 4.5 4.5	 60 30	mV_{PP}
−	Crosstalk Between Any Two Switches	$f_{in} \equiv$ Sine Wave Adjust f_{in} Voltage to Obtain 0 dBm at V_{IS} f_{in} = 10 kHz, R_L = 600 Ω, C_L = 50 pF f_{in} = 1.0 MHz, R_L = 50 Ω, C_L = 10 pF	 4.5 4.5	 −70 −80	dB
THD	Total Harmonic Distortion	f_{in} = 1 kHz, R_L = 10 kΩ, C_L = 50 pF $THD = THD_{Measured} - THD_{Source}$ V_{IS} = 4.0 V_{PP} sine wave	 4.5	 0.04	%
C_S	Switch Input Capacitance			5	pF
C_{COM}	Switch Common Capacitance			45	pF

*Limits not tested. Determined by design and verified by qualification.

TYPICAL CHARACTERISTICS

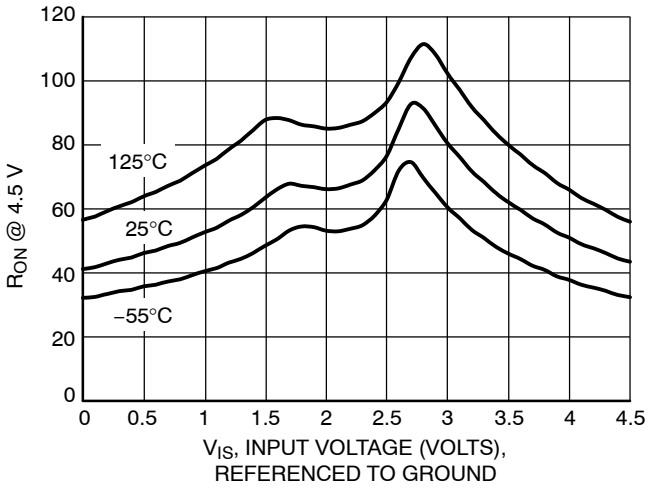


Figure 3. Typical On Resistance, V_{CC} = 4.5 V

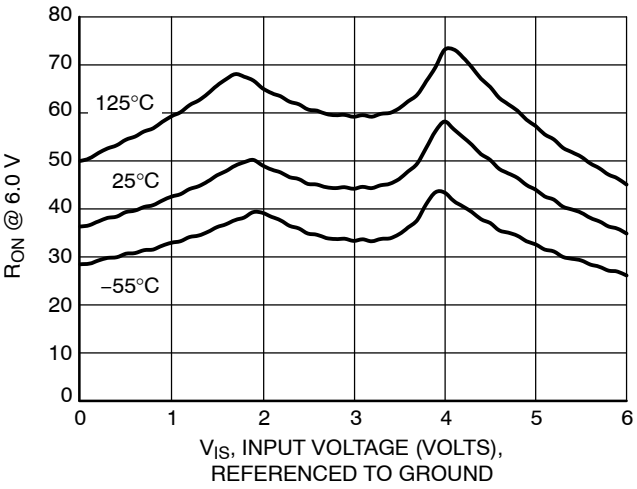


Figure 4. Typical On Resistance, V_{CC} = 6.0 V

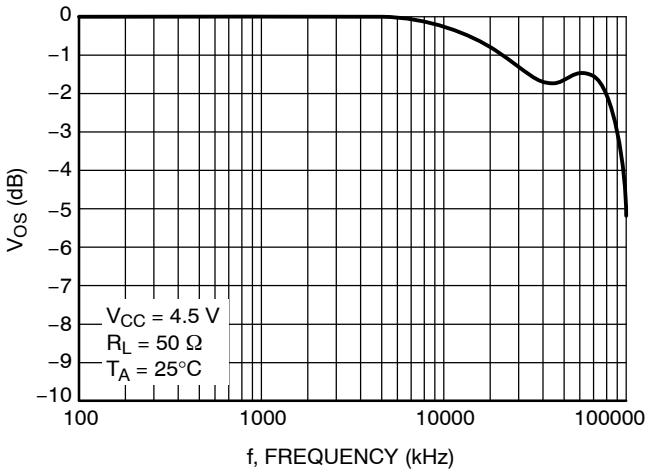


Figure 5. Typical Switch Frequency Response

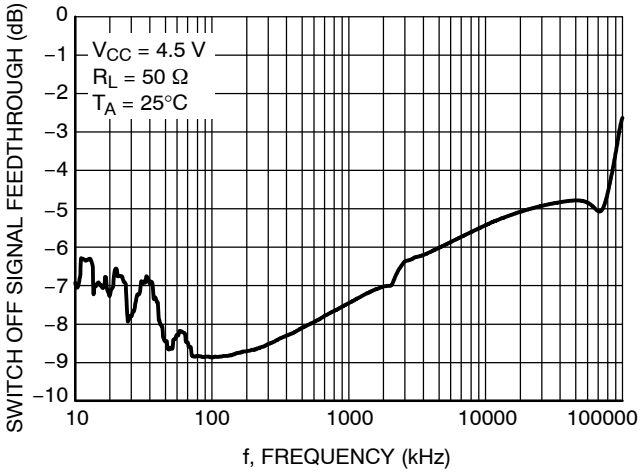


Figure 6. Typical Switch OFF Signal Feedthrough vs Frequency

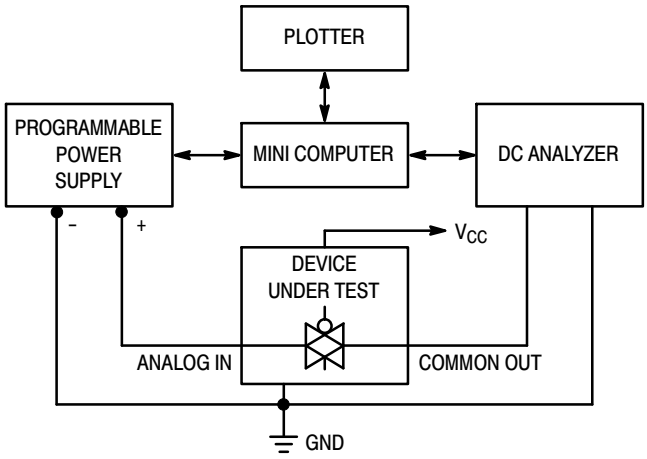


Figure 7. On Resistance Test Setup

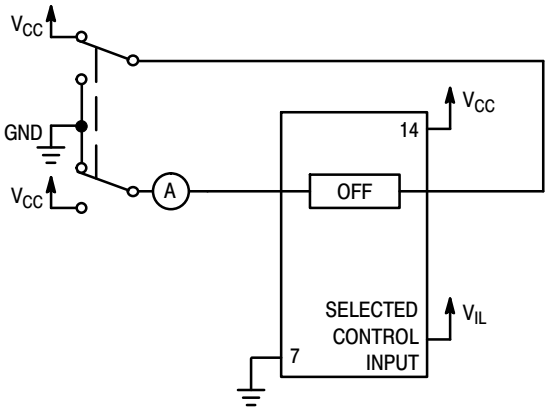


Figure 8. OFF Channel Leakage Current Test Setup, Any One Channel

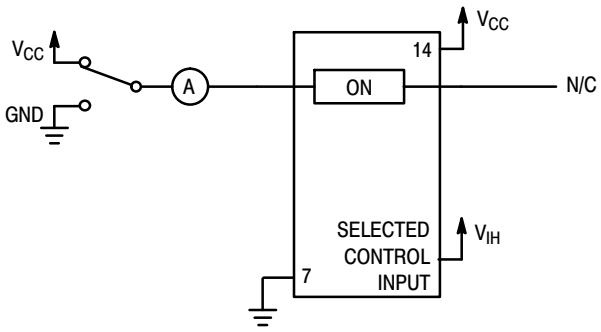


Figure 9. ON Channel Leakage Current Test Setup

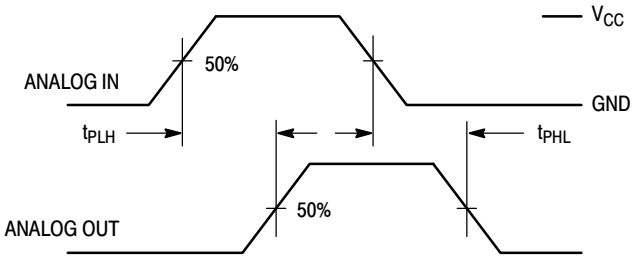
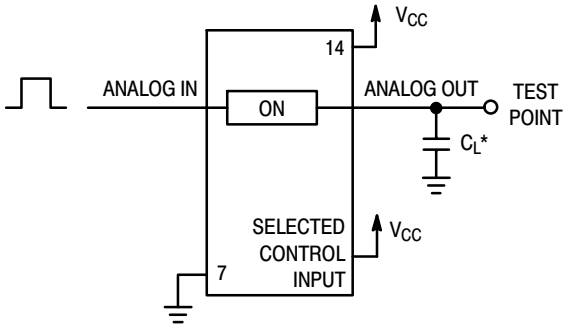


Figure 10. Propagation Delay, Analog In to Analog Out



*Includes all probe and jig capacitance.

Figure 11. Propagation Delay Test Setup

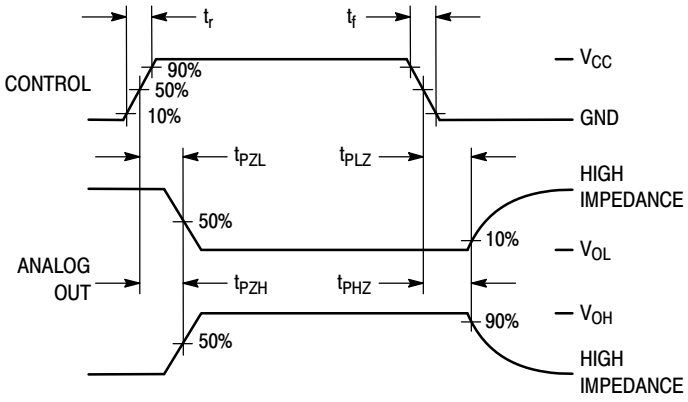
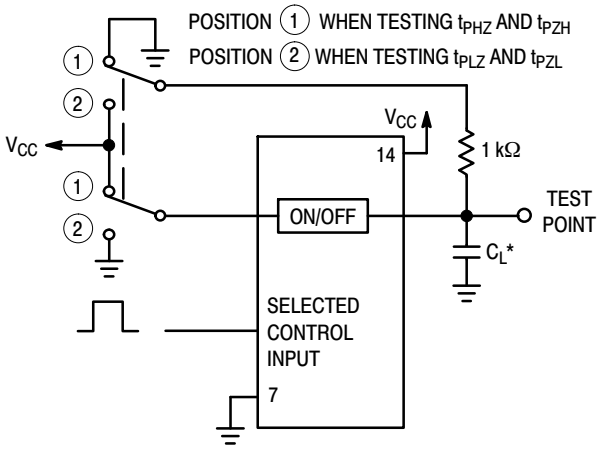


Figure 12. Turn−ON / Turn−OFF Times



*Includes all probe and jig capacitance.

Figure 13. Turn−ON / Turn−OFF Time Test Setup

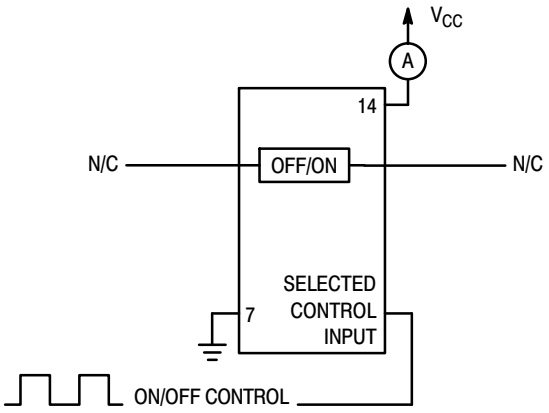
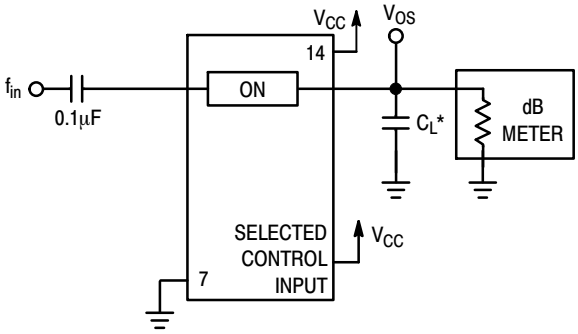
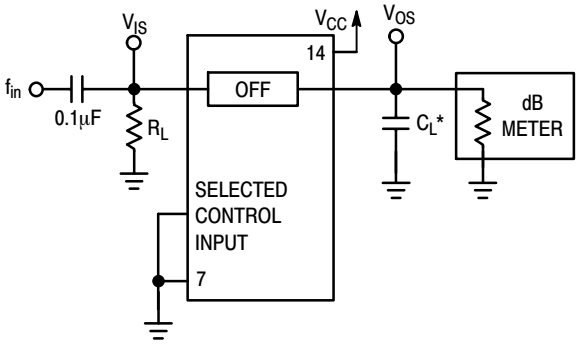


Figure 14. Power Dissipation Capacitance Test Setup



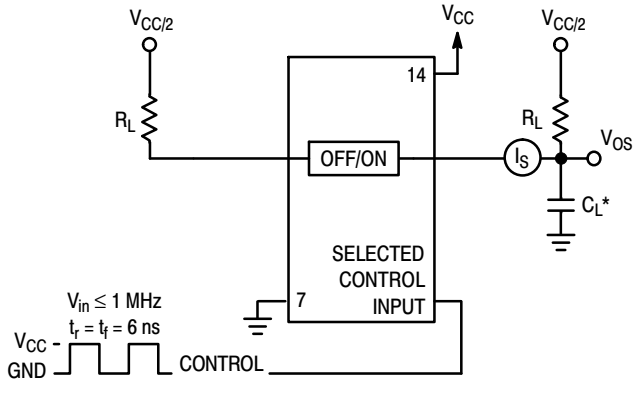
*Includes all probe and jig capacitance.

Figure 15. ON Channel Bandwidth Test Setup



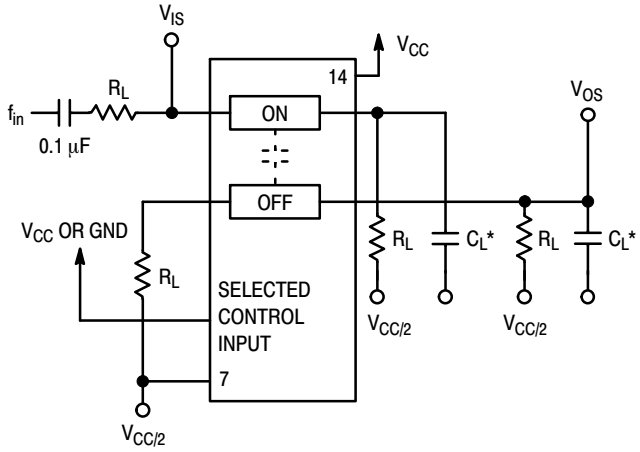
*Includes all probe and jig capacitance.

Figure 16. OFF Channel Feedthrough Isolation Test Setup



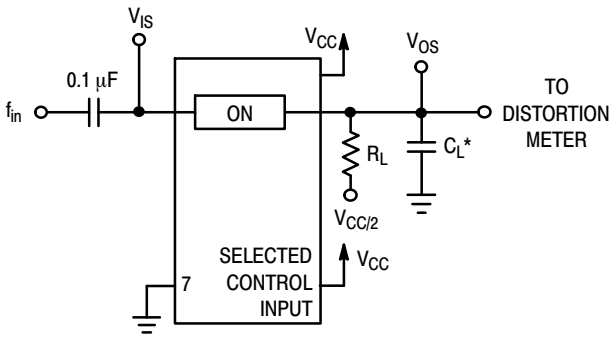
*Includes all probe and jig capacitance.

Figure 17. Feedthrough Noise Test Setup



*Includes all probe and jig capacitance.

Figure 18. Crosstalk Between Any Two Switches Test Setup



*Includes all probe and jig capacitance.

Figure 19. Total Harmonic Distortion Test Setup

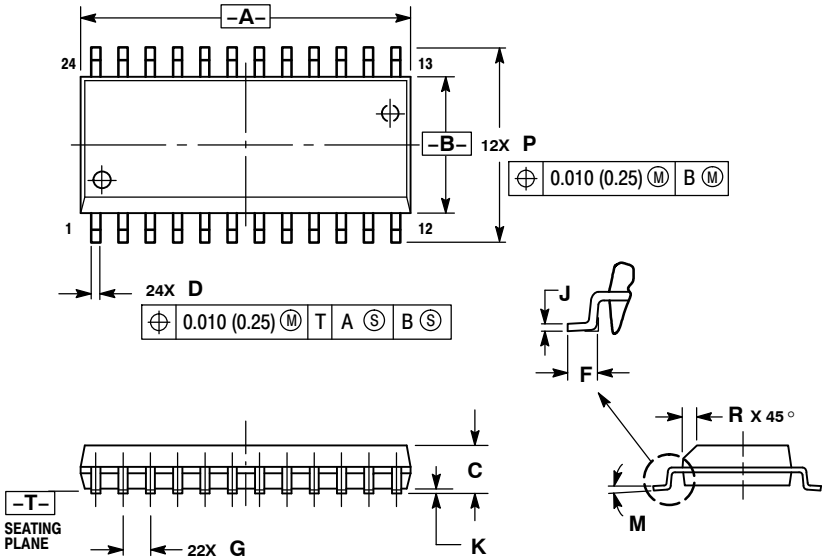
ORDERING INFORMATION

Device	Package	Shipping†
MC74HC4067ADWR2G	SOIC−24 (Pb−Free)	1000 / Tape & Reel
MC74HC4067ADTR2G	TSSOP−24*	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*This package is inherently Pb−Free.

PACKAGE DIMENSIONS

SOIC−24
CASE 751E−04
ISSUE E

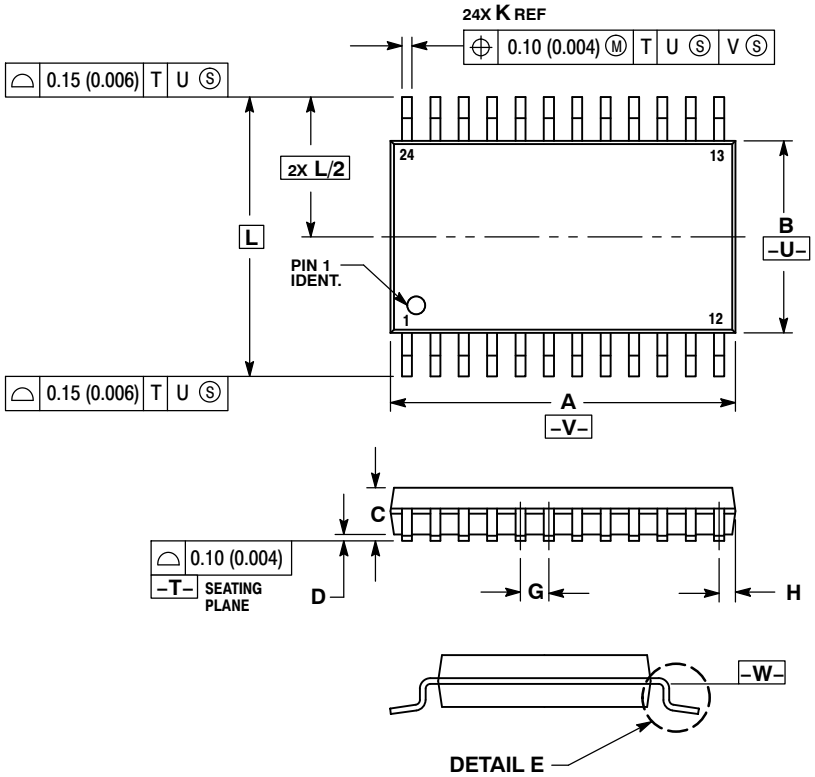


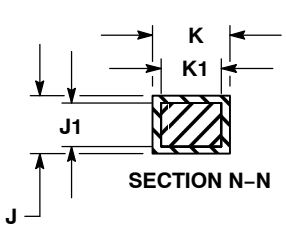
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.13 (0.005) TOTAL IN EXCESS OF D DIMENSION AT MAXIMUM MATERIAL CONDITION.

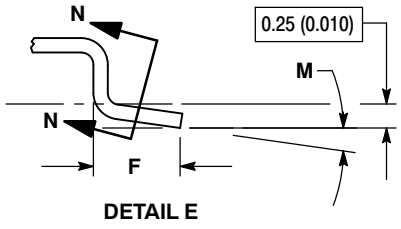
	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	15.25	15.54	0.601	0.612
B	7.40	7.60	0.292	0.299
C	2.35	2.65	0.093	0.104
D	0.35	0.49	0.014	0.019
F	0.41	0.90	0.016	0.035
G	1.27 BSC		0.050 BSC	
J	0.23	0.32	0.009	0.013
K	0.13	0.29	0.005	0.011
M	0°	8°	0°	8°
P	10.05	10.55	0.395	0.415
R	0.25	0.75	0.010	0.029

PACKAGE DIMENSIONS

TSSOP−24
CASE 948H−01
ISSUE A







NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	7.70	7.90	0.303	0.311
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
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